	Typ	L #	Hits	S arch T xt	DBs	Tim Stamp
1	BRS	L3	3144	MRAM or (magnetoresist$6 adj semiconductor adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:14
2	BRS	L4	67303	read/write	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:11
3	BRS	L5	1218	4 near4 current	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:11
4	BRS	L6	78	3 and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:12
5	BRS	L7	5060	write adj current	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:12

	Type	L #	Hits	S arch Text	DBs	Tim Stamp
6	BRS	L8	561	3 and 7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:12
7	BRS	L9	3751	MRAM or (magnetoresist$6 near4 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:14
8	BRS	L10	84	9 and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:13
9	BRS	L11	598	9 and 7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:14
10	BRS	L12	49921	(multilevel or multi-level or third or fourth) near2 line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:15

	Typ	L #	Hits	S arch Text	DBs	Time Stamp
11	BRS	L13	22561	selection near2 line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:15
12	BRS	L14	313	9 and 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:15
13	BRS	L16	85	14 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:16
14	IS&R	L18	2085	(438/622).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:22
15	IS&R	L17	225	(438/620).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 18:23

	Type	L #	Hits	Search T xt	DBs	Time Stamp
1	BRS	L1	3154	MRAM or (magnetoresist$6 adj semiconductor adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:10
2	BRS	L2	67313	read/write	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:10
3	BRS	L3	1218	read/write near4 current	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:10
4	BRS	L5	5061	write adj current	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:10
5	BRS	L6	562	(MRAM or (magnetoresist$6 adj semiconductor adj memory)) and (write adj current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:11

	Type	L #	Hits	Search T xt	DBs	Time Stamp
6	BRS	L7	3762	MRAM or (magnetoresist$6 near4 memory).	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/11 12:11
7	BRS	L8	84	(MRAM or (magnetoresist$6 near4 memory)) and (read/write near4 current)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/11 12:11
8	BRS	L10	49927	(multilevel or multi-level or third or fourth) near2 line	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/11 12:11
9	BRS	L11	22563	selection near2 line	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/11 12:11
10	BRS	L12	313	(MRAM or (magnetoresist$6 near4 memory)) and ((multilevel or multi-level or third or fourth) near2 line)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/11 12:11

	Type	L #	Hits	S arch Text	DBs	Tim Stamp
11	BRS	L4	78	(MRAM or (magnetoresist$6 adj semiconductor adj memory)) and (read/write near4 current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:11
12	BRS	L9	599	(MRAM or (magnetoresist$6 near4 memory)) and (write adj current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:11
13	BRS	L13	85	((MRAM or (magnetoresist$6 near4 memory)) and ((multilevel or multi-level or third or fourth) near2 line)) and (selection near2 line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:11
14	IS&R	L15	225	(438/620).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:11
15	BRS	L18	3775	MRAM or (magnetoresist$6 adj random adj access adj memory) or (magnetoresist$6 near2 RAM) or (magnetoresist$6 near4 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:16

	Typ	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L19	600	18 and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:17
17	BRS	L20	112	19 and 11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 13:21
18	IS&R	L21	2087	(438/622).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:43
19	BRS	L22	3	21 and 18	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:45
20	BRS	L23	2	15 and 18	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 12:45

	Type	L #	Hits	S arch Text	DBs	Tim Stamp
21	IS&R	L28	2	("6211559").PN.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/11 13:21
22	BRS	L32	1	30 and 11	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/11 13:28
23	BRS	L30	811	three adj dimensional adj circuit	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/11 13:28
24	BRS	L33	195	30 and (memory or ROM)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/11 13:29
25	BRS	L44	254228	three adj dimensional	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/11 14:15

	Typ	L #	Hits	Search Text	DBs	Time Stamp
26	BRS	L45	186	44 and MRAM	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 14:15
27	BRS	L46	497	magnetic adj ram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 14:36
28	BRS	L47	16	46 and 11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 14:36